

SLPS256A-MARCH 2010-REVISED OCTOBER 2010

30V N-Channel NexFET[™] Power MOSFET

Check for Samples: CSD17312Q5

FEATURES

- **Optimized for 5V Gate Drive**
- Ultra Low Q_a and Q_{ad}
- Low Thermal Resistance
- **Avalanche Rated**
- **Pb Free Terminal Plating**
- **RoHS Compliant**
- **Halogen Free**
- SON 5-mm × 6-mm Plastic Package

APPLICATIONS

- **Notebook Point-of-Load**
- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems

DESCRIPTION

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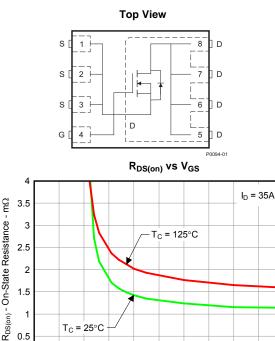
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The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.



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V_{GS} - Gate-to-Source Voltage - V

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PRODUCT SUMMARY

V _{DS}	Drain to Source Voltage	Source Voltage 30		V
Qg	Gate Charge Total (4.5V)	28		nC
Q _{gd}	Gate Charge Gate to Drain	6		nC
		$V_{GS} = 3V$	1.8	mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 4.5V 1.4		mΩ
		V _{GS} = 8V 1.2		mΩ
V _{GS(th)}	Threshold Voltage	1.1		V

ORDERING INFORMATION

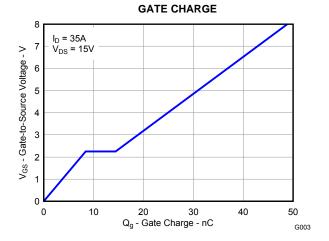
Device	Package	Media	Qty	Ship
CSD17312Q5	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 2$	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	+10 /8	V
	Continuous Drain Current, $T_C = 25^{\circ}C$	100	А
ID	Continuous Drain Current ⁽¹⁾	38	А
I _{DM}	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	200	А
PD	Power Dissipation ⁽¹⁾	3.2	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, Single Pulse $I_D = 130A$, L = 0.1mH, $R_G = 25\Omega$	845	mJ

(1) Typical $R_{\theta JA}$ = 39°C/W when mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.

(2) Pulse duration ≤300µs, duty cycle ≤2%



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 $T_C = 25^{\circ}C$

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CSD17312Q5



XAS STRUMENTS

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

PARAMETER		TEST CONDITIONS	MIN TYP	MAX	UNIT
Static Cl	haracteristics				
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	30		V
I _{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 24V$		1	μA
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +10/-8V$		100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.9 1.1	1.5	V
		V _{GS} = 3V, I _D = 35A	1.8	2.4	mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 4.5V, I _D = 35A	1.4	1.7	mΩ
		V _{GS} = 8V, I _D = 35A	1.2	1.5	mΩ
9 _{fs}	Transconductance	V _{DS} = 15V, I _D = 35A	200		S
Dynamic	Characteristics		·		
C _{iss}	Input Capacitance		4030	5240	pF
C _{oss}	Output Capacitance	$V_{GS} = 0V, V_{DS} = 15V,$ f = 1MHz	2220	2890	pF
C _{rss}	Reverse Transfer Capacitance		93	120	pF
R _G	Series Gate Resistance		1.1	2.2	Ω
Qg	Gate Charge Total (4.5V)		28	36	nC
Q _{gd}	Gate Charge Gate to Drain	V _{DS} = 15V,	6		nC
Q _{gs}	Gate Charge Gate to Source	I _{DS} = 35A	8.4		nC
Q _{g(th)}	Gate Charge at Vth		4.4		nC
Q _{oss}	Output Charge	$V_{DS} = 14.8V, V_{GS} = 0V$	57		nC
t _{d(on)}	Turn On Delay Time		9.5		ns
t _r	Rise Time	V _{DS} = 15V, V _{GS} = 4.5V,	27		ns
t _{d(off)}	Turn Off Delay Time	$I_{DS} = 35A, R_G = 2\Omega$	35		ns
t _f	Fall Time		23		ns
Diode Cl	haracteristics	· · ·			
V _{SD}	Diode Forward Voltage	$I_{SD} = 35A, V_{GS} = 0V$	0.8	1	V
Q _{rr}	Reverse Recovery Charge	V _{DD} = 14.8V, I _F = 35A,	88		nC
t _{rr}	Reverse Recovery Time	di/dt = 300A/µs	43		ns

THERMAL CHARACTERISTICS

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$							
	PARAMETER	MIN	TYP	MAX	UNIT		
R_{\thetaJC}	Thermal Resistance Junction to Case ⁽¹⁾			1	°C/W		
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾			49	°C/W		

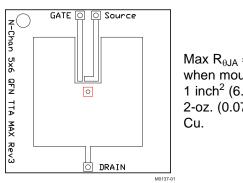
 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu. (1)

(2)

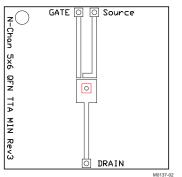


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Max $R_{\theta JA} = 49^{\circ}C/W$ when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta,JA} = 119^{\circ}C/W$ when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

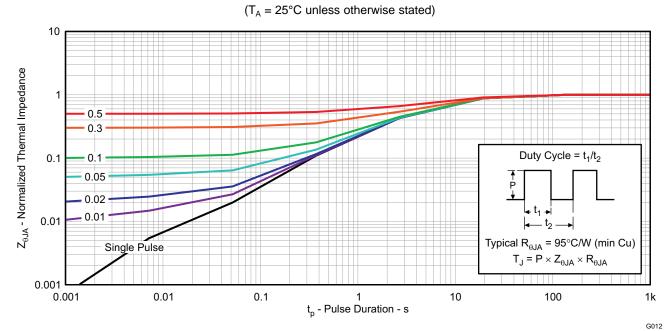


Figure 1. Transient Thermal Impedance

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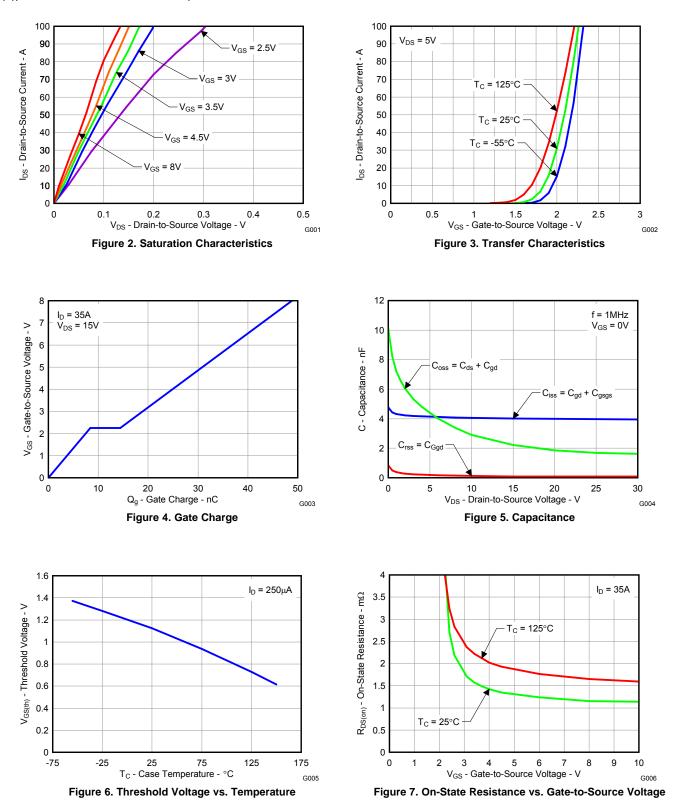
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STRUMENTS

EXAS

TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$





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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

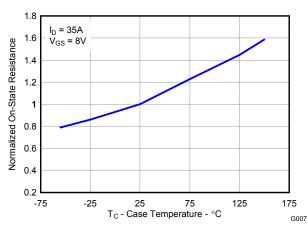
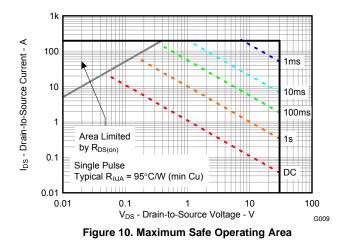


Figure 8. Normalized On-State Resistance vs. Temperature



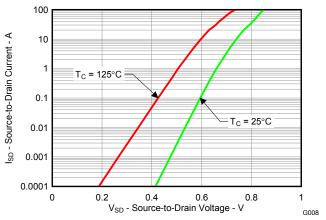


Figure 9. Typical Diode Forward Voltage

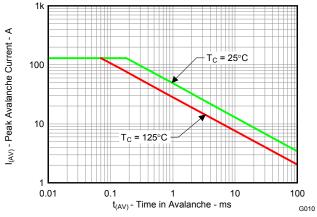


Figure 11. Single Pulse Unclamped Inductive Switching

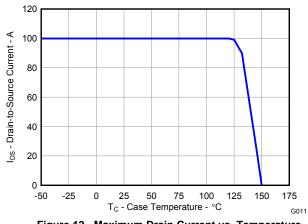


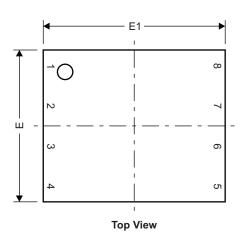
Figure 12. Maximum Drain Current vs. Temperature

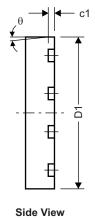
TEXAS INSTRUMENTS

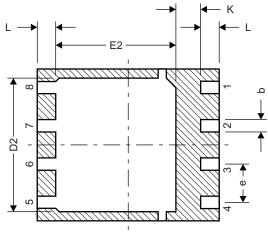
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MECHANICAL DATA

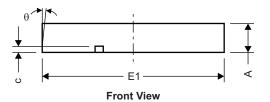
Q5 Package Dimensions







Bottom View



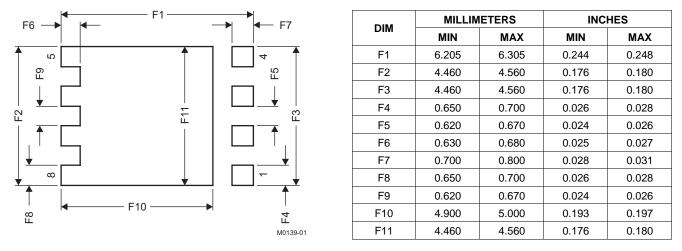
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DIM	MILLIN	IETERS	INCHES		
DIW	MIN	MAX	MIN	MAX	
A	0.950	1.050	0.037	0.039	
b	0.360	0.460	0.014	0.018	
с	0.150	0.250	0.006	0.010	
c1	0.150	0.250	0.006	0.010	
D1	4.900	5.100	0.193	0.201	
D2	4.320	4.520	0.170	0.178	
E	4.900	5.100	0.193	0.201	
E1	5.900	6.100	0.232	0.240	
E2	3.920	4.12	0.154	0.162	
е	1.27	TYP	0.0	50	
К	0.760		0.030		
L	0.510	0.710	0.020	0.028	
θ	0.00				



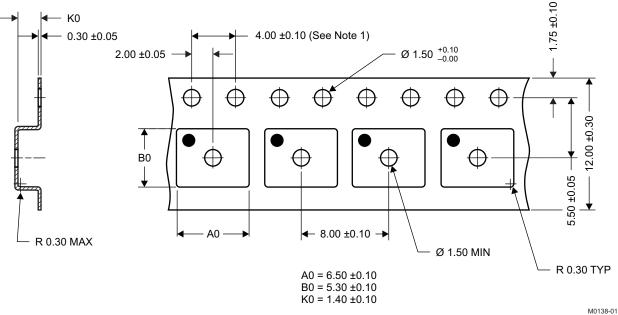
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Recommended PCB Pattern



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5 Tape and Reel Information



Notes: 1. 10-sprocket hole-pitch cumulative tolerance ± 0.2

2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm

- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. Thickness: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and convection) PbF reflow compatible

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REVISION HISTORY

Cł	nanges from Original (March 2010) to Revision A	Page
•	Deleted the Package Marking Information section	7



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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal				
Device	Package	Package	SPQ	Reel

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD17312Q5	SON	DQH	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

31-Oct-2013



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD17312Q5	SON	DQH	8	2500	335.0	335.0	32.0

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